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PATENT & TRADEMARK OFFICE

DOCKET NO. 003330 USA/ETCH/METAL/JB

APPLICATION NO.:
10/042,666

FORM PTO-1449

U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICEINFORMATION DISCLOSURE STATEMENT
IN AN APPLICATION
(Use several sheets if necessary)

APPLICANT: Han, et al.

FILING DATE: 1/8/2002

GROUP ART UNIT:
Unknown

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER							DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
ML	4	8	9	7	3	1	5	1/30/1990	Gupta	428	552	
ML	4	9	3	9	3	0	8	7/3/1990	Maxfield et al.	505	1	
ML	4	9	3	3	2	3	9	6/12/1990	Olson et al.	428	557	
ML	4	9	1	0	0	9	2	3/20/1990	Olson et al.	428	557	
ML	5	2	4	4	8	7	5	9/14/1993	Hauser et al.	505	1	
ML	5	4	7	0	8	2	0	11/28/1995	Hauser et al.	505	472	
ML	5	8	2	4	2	0	5	10/20/1998	Foster	205	109	
ML	5	8	3	3	8	2	9	11/10/1998	Foster	205	109	
ML	6	3	0	6	2	7	6	10/23/2001	Nobe et al.	205	238	

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER							DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
												YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)

ML	Hart, Anthony C, Alloy plating problem cracked, Nickel Magazine, June 1998
	Praxair, Tribomet MCrAlY Coatings, Praxair Surface Technologies Ltd, 2002, Available at: http://www.praxair.com/praxair.nsl/d63afe71c771b0d785256519006c5ea1/cccb361d6209c12b852565550043ee8d/\$FILE/MCrAlYco.pdf , Accessed 29 April 2002.

EXAMINER

DATE CONSIDERED

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICE

DOCKET NO. 003330/ETCH/METAL/JB

APPLICATION
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APPLICANT: Han, et al.

FILING DATE: Herewith

GROUP ART UNIT

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER							DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
<i>ML</i>	4	2	4	4	7	4	3	01/13/81	Blackburn, et al.	106	55	
<i>ML</i>	4	7	4	3	4	9	3	5/10/88	Sioshansi, et al.	428	217	
<i>ML</i>	4	9	7	3	4	4	5	11/27/90	Singheiser, et al.	420	443	
<i>ML</i>	5	3	6	6	5	8	5	11/22/94	Robertson, et al.	156	643	
<i>ML</i>	5	4	9	8	3	1	3	03/12/96	Bailey, et al.	156	643.1	
<i>ML</i>	5	6	2	4	6	3	2	4/29/97	Baumann, et al.	420	544	
<i>ML</i>	5	6	8	0	0	1	3	10/21/97	Dornfest, et al.	315	111.21	
<i>ML</i>	5	7	5	3	0	4	4	05/19/98	Hanawa, et al.	118	723 I	
<i>ML</i>	5	7	9	8	0	1	6	08/25/98	Oehrlein, et al.	156	345	
<i>ML</i>	5	9	4	8	5	1	3	09/07/99	Kriven, et al.	428	216	
<i>ML</i>	5	9	6	4	9	2	8	10/12/99	Tomlinson, et al.	106	14.21	
<i>ML</i>	6	21	22	3	7	9	1	12/26/00	Han, et al.	156	1	
<i>ML</i>	6	2	3	1	8	0	8	05/15/01	Hashikura, et al.	420	528	

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER							DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
												YES	NO
<i>ML</i>	9	8	1	4	9	8	0	04/09/98	PCT	<i>/</i>	<i>/</i>	x	
<i>ML</i>	9	4	2	1	6	7	1	08/22/96	Germany	<i>/</i>	<i>/</i>		x
<i>ML</i>	08	4	9	7	6	7	A2	06/24/98	Europe	<i>/</i>	<i>/</i>	x	
<i>ML</i>	35	4	3	8	0	2	A1	06/19/87	Germany	<i>/</i>	<i>/</i>		x
<i>ML</i>	20	09	6	1	7	6	A2	4/4/00	Japan	<i>/</i>	<i>/</i>	Abstract	
<i>ML</i>	9	9	7	5	4	6	A1	5/3/00	Europe	<i>/</i>	<i>/</i>	x	
<i>ML</i>	43	3	3	5	7	3	A2	11/20/92	Japan	<i>/</i>	<i>/</i>	Abstract	
<i>ML</i>	1	6	4	5	7	2	A2	6/16/00	Japan	<i>/</i>	<i>/</i>	x	
<i>ML</i>	11	0	2	9	3	7	8	2/2/99	Japan	<i>/</i>	<i>/</i>	Abstract	
<i>ML</i>	10	0	6	7	5	5	4	03/10/98	Japan	<i>/</i>	<i>/</i>	Abstract	

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)

<i>ML</i>	An article entitled, "The evolution of DRAM cell technology," Solid State Technology 89-101 (May 1997), El-Kareh, et al.
<i>ML</i>	PCT Communication dated 11/25/99, European Patent Office, P.B 5818 Patentlaan, NL-2280 HV Rijswijk

EXAMINER

ML

DATE CONSIDERED

6/6/03

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